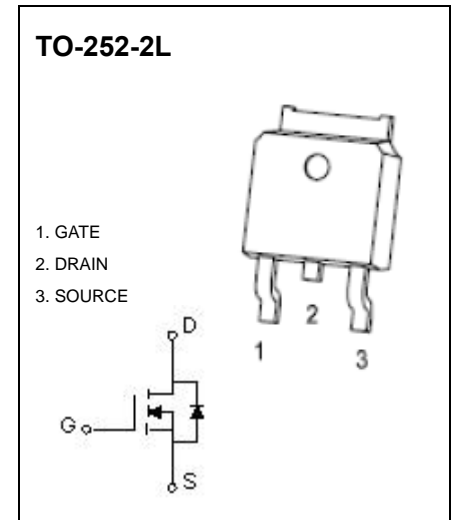


TO-252-2L Plastic-Encapsulate MOSFETS

CJU02N60 N-Channel Power MOSFET

General Description

The high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power suppliers, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.



FEATURES

- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	2	A
Pulsed Drain Current	I_{DM}	8	
Power Dissipation	P_D	1.25	W
Single Pulsed Avalanche Energy*	E_{AS}	128	mJ
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50 ~+150	

* E_{AS} condition: $T_J=25^\circ\text{C}$, $V_{DD}=50\text{V}$, $L=64\text{mH}$, $I_{AS}=2\text{A}$, $R_G=25\Omega$

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{(BR) DSS}	V _{GS} = 0V, I _D =250μA	600			V
Gate-Threshold Voltage (note1)	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	
Gate-Body Leakage Current (note1)	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =600V, V _{GS} =0V			25	μA
Drain-Source On-State Resistance (note1)	R _{DS(on)}	V _{GS} =10V, I _D =1A			4.4	Ω
Forward Transconductance (note1)	g _{FS}	V _{DS} =50V, I _D =1A	1			S
Input Capacitance (note2)	C _{iss}	V _{DS} =25V, V _{GS} =0V, f =1MHz		435		pF
Output Capacitance (note2)	C _{oss}			56		
Reverse Transfer Capacitance (note2)	C _{rss}			9.2		
Turn-On Delay Time (note2)	t _{d(on)}	V _{DD} =300V, I _D =2A, V _{GS} =10V, R _G =18Ω		12		ns
Rise Time (note2)	t _r			21		
Turn-Off Delay Time (note2)	t _{d(off)}			30		
Fall Time (note2)	t _f			24		
Forward on Voltage(note1)	V _{SD}	V _{GS} =0V, I _S =2A			1.6	V

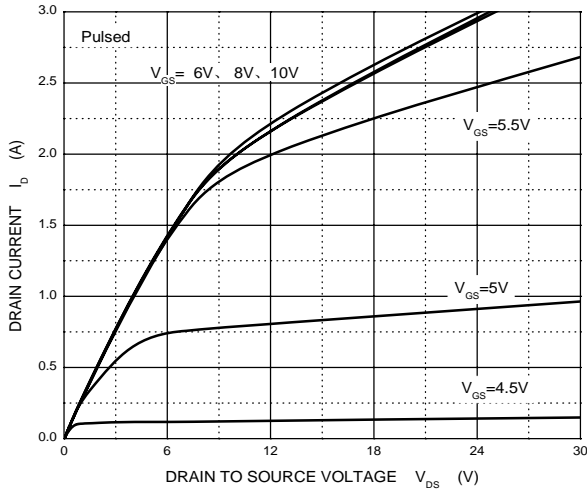
Notes:

1. Pulse Test : Pulse Width≤300μs, duty cycle ≤2%.
2. These parameters have no way to verify.

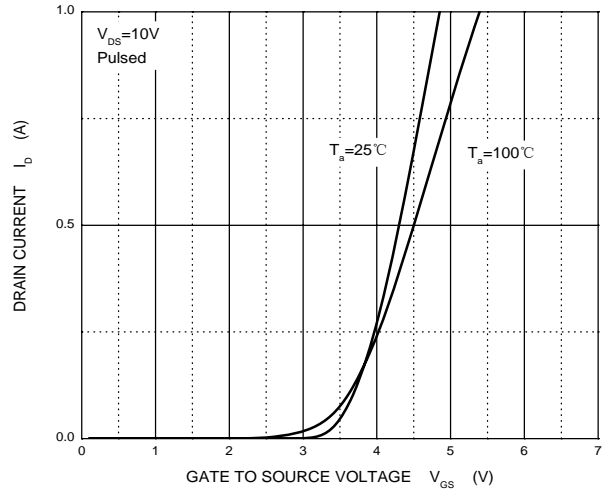
Typical Characteristics

CJU02N60

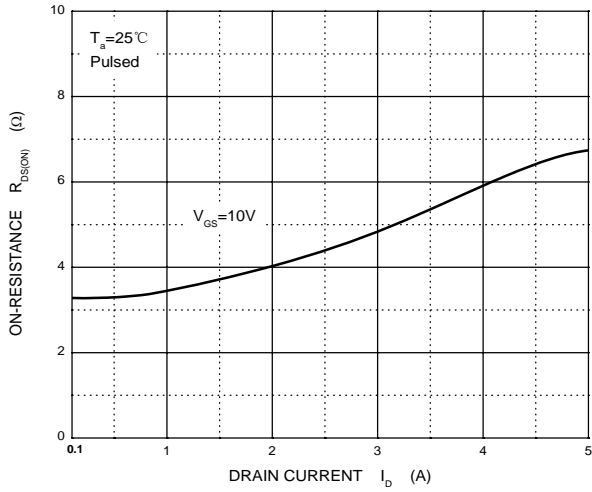
Output Characteristics



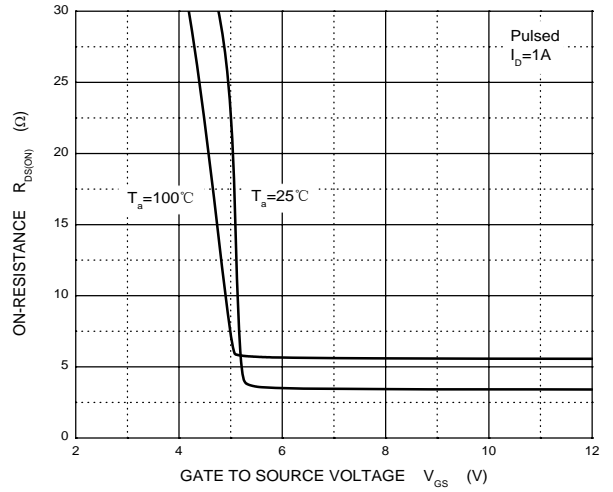
Transfer Characteristics



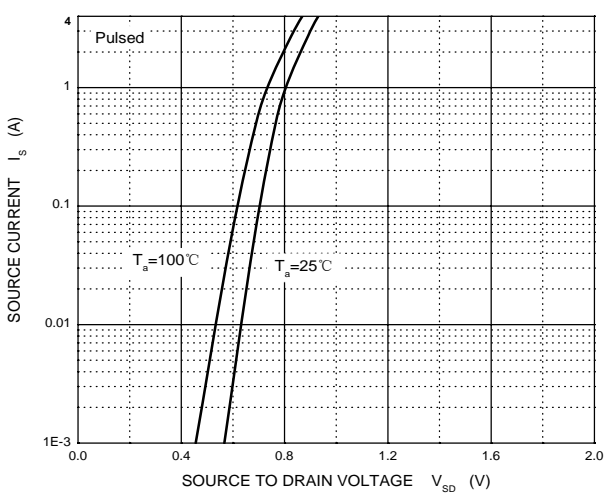
$R_{DS(ON)}$ — I_D



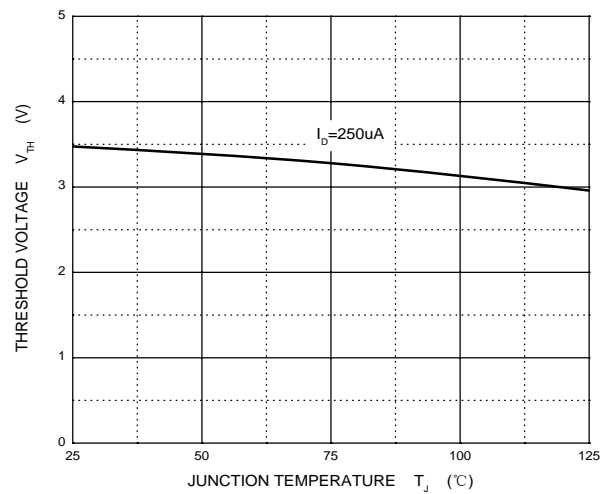
$R_{DS(ON)}$ — V_{GS}



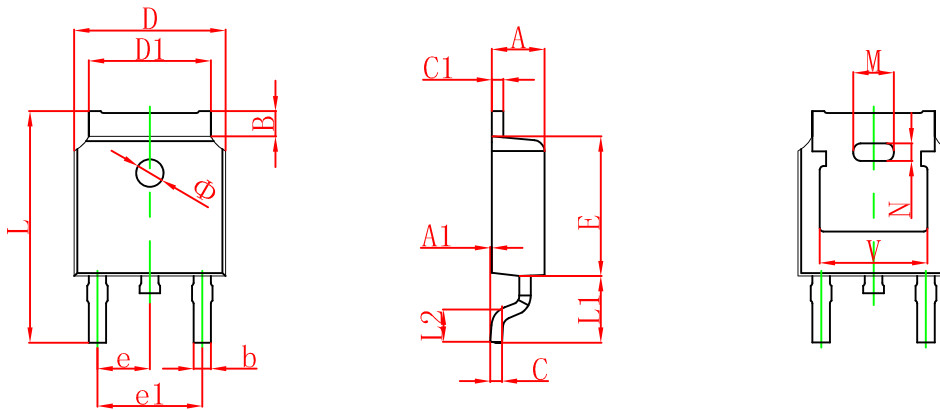
I_S — V_{SD}



Threshold Voltage

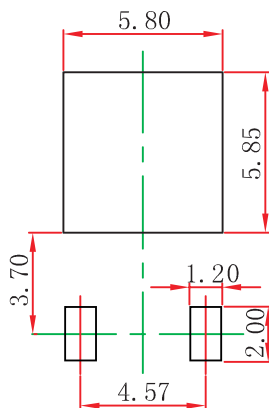


TO-252(4R)-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

TO-252(4R)-2L Suggested Pad Layout



Note:

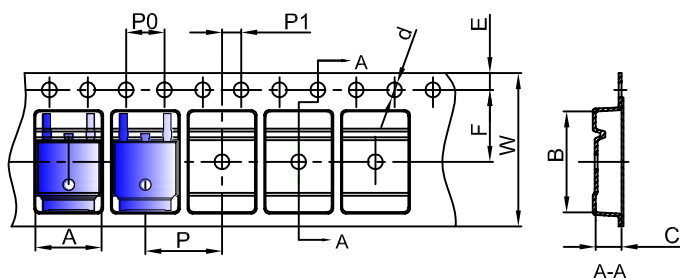
1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

TO-252 Tape and reel

TO-252 Embossed Carrier Tape

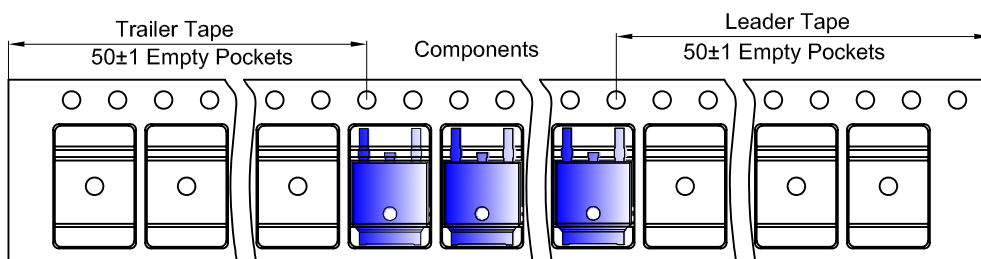


Packaging Description:

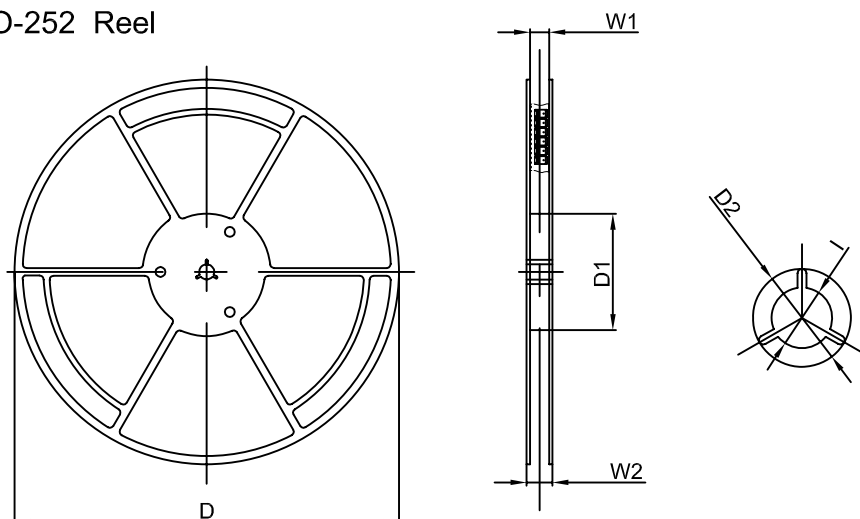
TO-252 parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 25,00 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00
(Tolerance)	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+/-0.1	+0.3/-0.1

TO-252 Tape Leader and Trailer



TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00
Tolerance	+/-2	+/-1	+/-1	+/-1	+/-1	+/-1

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	14.04